

☐ Drafts
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 L1: (1730) KRAM
 L2: (295) L1 and (second near3 magnetic near3 layer)
 L3: (11) L2 and (dummy near3 cell)
☒ Failed
☒ Saved
 (135369) memory and magnetic
 (5) (memory and magnetic) and ((first and second) with (magnetic adj3
 (15) (memory and magnetic) and (magnetic adj3 layer) and (insulat53 ne
 (161) (memory adj2 cell) and (insulat53 near3 film) and (magnet58 near
 (161) (memory adj2 cell) and (magnet magnetic) and (insulat53 near3 f:
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USPAT, US POPUS, EPG, JPO, DERWENT, BM, 108
 Default operator: OR
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A BRS Item A Set Item Page Text HTML

		Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C						
1	<input type="checkbox"/>	US 2003030935 A1	20030515	48	Thin film magnetic memory device for programming	365/171			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
2	<input type="checkbox"/>	US 2003038145 A1	20030501	39	Thin film magnetic memory device having data read	365/173	365/158; 365/171		Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
3	<input type="checkbox"/>	US 20030031046 A1	20030213	29	Thin film magnetic memory device realizing both	365/171			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
4	<input type="checkbox"/>	US 20030031045 A1	20030213	19	Magnetic random access memory including memory cell	365/158			Hosotani, Keiji	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
5	<input type="checkbox"/>	US 20030026125 A1	20030206	72	Thin film magnetic memory device including memory	365/158			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
6	<input type="checkbox"/>	US 20020172073 A1	20021121	69	Thin film magnetic memory device capable of conducting	365/158			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>
7	<input type="checkbox"/>	US 20020172058 A1	20021121	59	Thin film magnetic memory device having a magnetic	365/100			Hidaka, Hideto	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>

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L Number	Hits	Search Text	DB	Time stamp
1	1730	MRAM	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/24 17:08
2	295	MRAM and (second near3 magnetic near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/24 17:09
3	11	(MRAM and (second near3 magnetic near3 layer)) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/08/24 17:09
-	135369	memory and magnetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 11:43
-	5	(memory and magnetic) and ((first and second) with (magnetic adj3 layer)) and (insulat\$3 near3 film) and (reference near3 voltage) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 11:52
-	15	(memory and magnetic) and (magnetic adj3 layer) and (insulat\$3 near3 film) and (reference near3 voltage) and (dummy near3 cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 12:05
-	161	(memory adj2 cell) and (insulat\$3 near3 film) and (magnet\$8 near3 direction) and (magnet\$8 near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 12:08
-	161	(memory adj2 cell) and (magnet magnetic) and (insulat\$3 near3 film) and (magnet\$8 near3 direction) and (magnet\$8 near3 layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/02/11 12:08